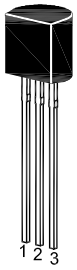
ST 2SC4002

NPN Silicon Epitaxial Planar Transistor

for High-Voltage Driver Applications.

The transistor is subdivided into two groups, D and E, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	400	V
Collector Emitter Voltage	V_{CEO}	400	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	200	mA
Collector Current (Pulse)	I_{CP}	400	mA
Power Dissipation	P_{tot}	600	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter			Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V_{CE} = 10 V, I_C = 50 mA	Current Gain Group	D	h_{FE}	60	-	120	-
		E	h_{FE}	100	-	200	-
Collector Base Cutoff Current at V_{CB} = 300 V			I_{CBO}	-	-	0.1	µA
Emitter Base Cutoff Current at V_{EB} = 4 V			I_{EBO}	-	-	0.1	µA
Collector Emitter Saturation Voltage at I_C = 50 mA, I_B = 5 mA			$V_{CE(sat)}$	-	-	0.6	V
Base Emitter Saturation Voltage at I_C = 50 mA, I_B = 5 mA			$V_{BE(sat)}$	-	-	1.0	V
Gain Bandwidth Product at V_{CE} = 30 V, I_C = 10 mA			f_T	-	70	-	MHz